DSC2001

Silicon NPN epitaxial planar type

For general amplification Complementary to DSA2001

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V _{CBO}	60	V					
Collector-emitter voltage (Base open)	V _{CEO}	50	V					
Emitter-base voltage (Collector open)	V _{EBO}	7	V					
Collector current	I _C	100	mA					
Peak collector current	I _{CP}	200	mA					
Collector power dissipation	P _C	200	mW					
Junction temperature	Tj	150	°C					
Storage temperature	T _{stg}	-55 to +150	°C					

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f _T	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Code	R	S	0
Rank	R	S	No-rank
$h_{\rm FE}$	210 to 340	290 to 460	210 to 460
Marking Symbol	C1R	C1S	C1

Product of no-rank is not classified and have no marking symbol for rank.

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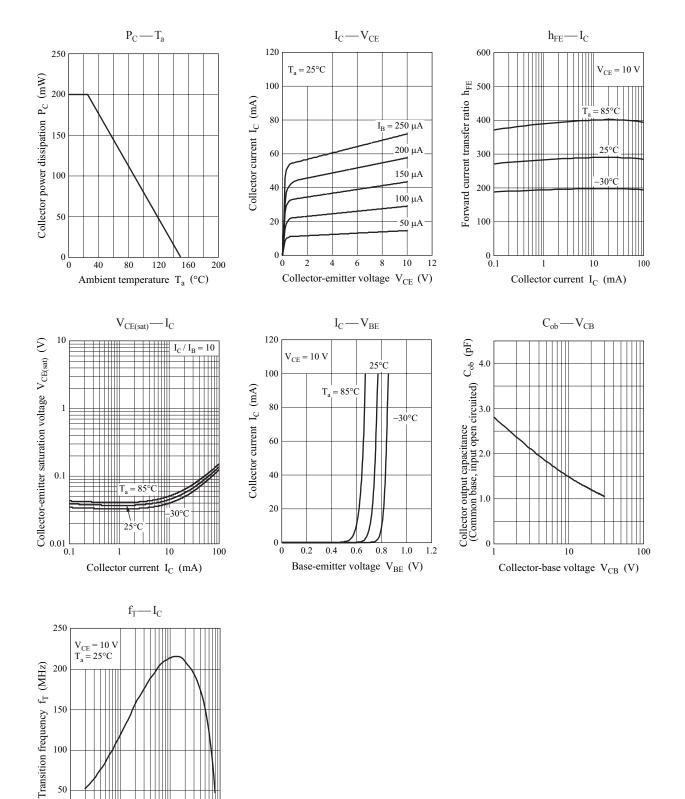
Package

- Code
- Mini3-G3-B
- Pin Name
 - 1. Base
 - 2. Emitter
 - 3. Collector

Marking Symbol: C1

DSC2001

Panasonic



50

0 ∟ 0.1

10

Collector current I_C (mA)

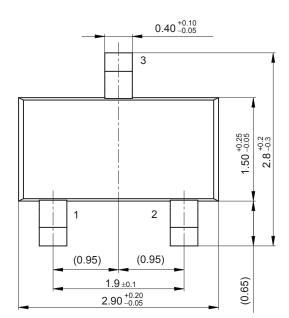
1

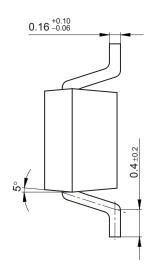
100

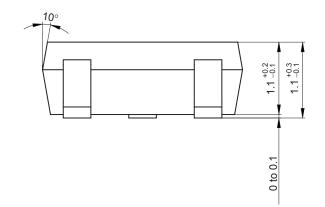
Panasonic

Mini3-G3-B

Unit: mm







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